

CLEAN REPLACEMENT PARAGRAPH

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Pretreating a substrate surface with iodine has been reported to increase the growth rate of copper deposited by a MOCVD technique using Cu(hfac)TMVS precursor. United States Patent No. 6,413,864 issued July 2, 2002 to Pyo et al., discloses forming a copper seed layer on a nitride barrier layer surface (e.g., TiN, TaN, WN), then forming a chemical enhancement layer (CE layer) with an iodine-containing liquid compound prior to forming a first copper layer by MOCVD, and then electroplating a second copper layer onto the first copper layer. United States Patent No. 6,468,907 issued October 22, 2002 to Pyo et al., discloses forming a CE layer on a nitride barrier layer surface (e.g., TiN, TaN, WN) with an iodine-containing liquid or gas (or F, Cl, Br, I or At gas), and then removing part of the CE layer prior to filling a damascene pattern with a copper (or Al or W) layer using MOCVD. United States Patent No. 6,593,236 issued July 15, 2003 to Pyo et al., discloses forming a CE layer on a copper seed layer with an iodine-containing liquid or gas (or F, Cl, Br, I or At gas), then removing part of the CE layer by plasma while partially filling a damascene pattern with a copper layer using MOCVD, then electroplating copper. A CE layer of Pyo et al. accelerates or increases the deposition rate of copper onto the CE layer compared to portions of the substrate having no CE layer.